

IN THE CLAIMS:

Please amend claims 1, 4, 5 and 7 as follows:

Sub B1

1. A semiconductor memory device, including a copper fuse section that is oxidized by a laser beam in an oxidizing environment, comprising:
a dielectric film including a first film section formed on a substrate, a second film section formed on said first film section, and a third film section formed over said second film section;
a wiring line structure, including:
a first and a second wiring line, each of said first and second wiring lines formed on said second film section of said dielectric film and extending in an opposite direction, and
said copper fuse section formed on said first film section of said dielectric film, an end of said copper fuse section being connected to said first wiring line and another end of said copper fuse section being connected to said second wiring line; and
an opening formed in said third and second film sections of said dielectric film and between said first and second wiring lines, wherein said opening provides access to said laser beam to oxidize said copper fuse section in said oxidizing environment.

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4 (Amended) A semiconductor memory device according to claim 1, wherein at least one of said first and second wiring lines includes copper.

5. (Amended) A semiconductor memory device according to claim 2, wherein at least one of said first and second wiring lines includes copper.

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7. (Amended) A semiconductor memory device according to claim 1, further comprising a wiring line formed on said first section of said dielectric film.

Please add claims 15 and 16 as follows:

A5

--15. A semiconductor memory device according to claim 7, wherein said wiring line includes copper.